Dual P-Channel 30-V (D-S) MOSFET

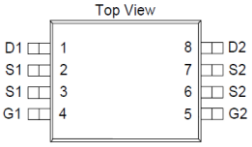
Key Features:
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

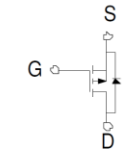
Typical Applications:
- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (mΩ)	I_D (A)
-30	50 @ V_{GS} = -10V	-4.2
	72 @ V_{GS} = -4.5V	-3.5

Pb-free
RoHS COMPLIANT
HALOGEN FREE

TSSOP-8
Top View





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current [a]	T_A=25°C	I_D	-4.2	A
	T_A=70°C		-3.3	
Pulsed Drain Current [b]		I_{DM}	-20	
Continuous Source Current (Diode Conduction) [a]		I_S	-1.7	A
Power Dissipation [a]	T_A=25°C	P_D	1.3	W
	T_A=70°C		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient [a]	t <= 10 sec	$R_{\theta JA}$	100	°C/W
	Steady State		166	

Notes
a. Surface Mounted on 1” x 1” FR4 Board.
b. Pulse width limited by maximum junction temperature

Electrical Characteristics

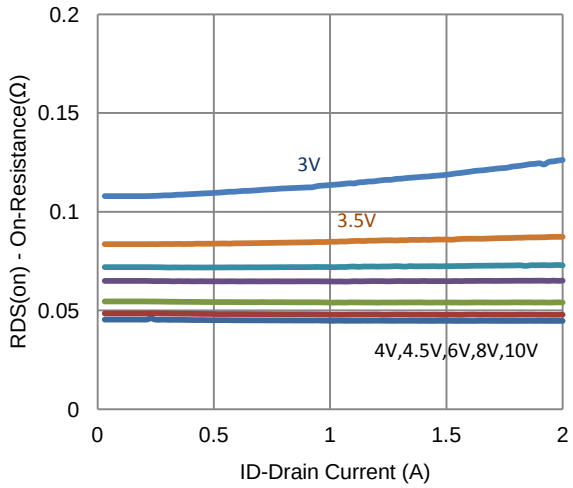
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 uA	-1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24 V, V_{GS} = 0 V			-1	uA
		V_{DS} = -24 V, V_{GS} = 0 V, T_J = 55°C			-10	
On-State Drain Current [a]	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -10 V	-6.3			A
Drain-Source On-Resistance [a]	$r_{DS(on)}$	V_{GS} = -10 V, I_D = -2 A			50	mΩ
		V_{GS} = -4.5 V, I_D = -1.6 A			72	
Forward Transconductance [a]	g_{fs}	V_{DS} = -15 V, I_D = -2 A		6		S
Diode Forward Voltage [a]	V_{SD}	I_S = -0.9 A, V_{GS} = 0 V		-0.77		V
Dynamic [b]						
Total Gate Charge	Q_g	V_{DS} = -15 V, V_{GS} = -4.5 V, I_D = -2 A		9		nC
Gate-Source Charge	Q_{gs}			3.3		
Gate-Drain Charge	Q_{gd}			2.8		
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = -15 V, R_L = 7.5 Ω, I_D = -2 A, V_{GEN} = -10 V, R_{GEN} = 6 Ω		6		ns
Rise Time	t_r			7		
Turn-Off Delay Time	$t_{d(off)}$			44		
Fall Time	t_f			19		
Input Capacitance	C_{iss}	V_{DS} = -15 V, V_{GS} = 0 V, f = 1 Mhz		787		pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			73		

Notes

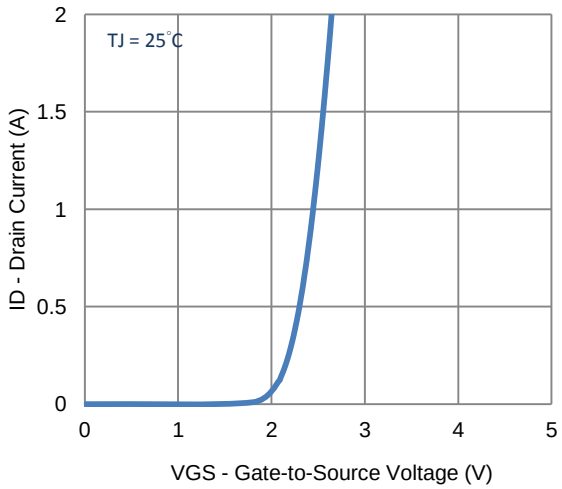
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

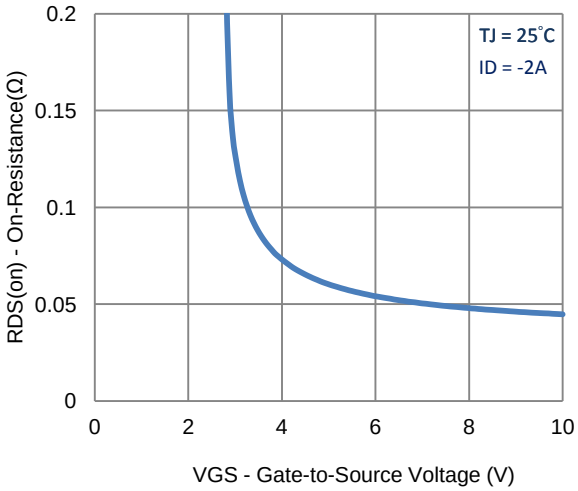
Typical Electrical Characteristics



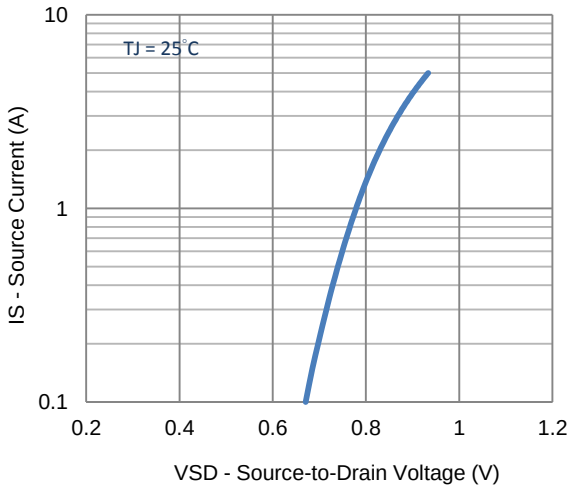
1. On-Resistance vs. Drain Current



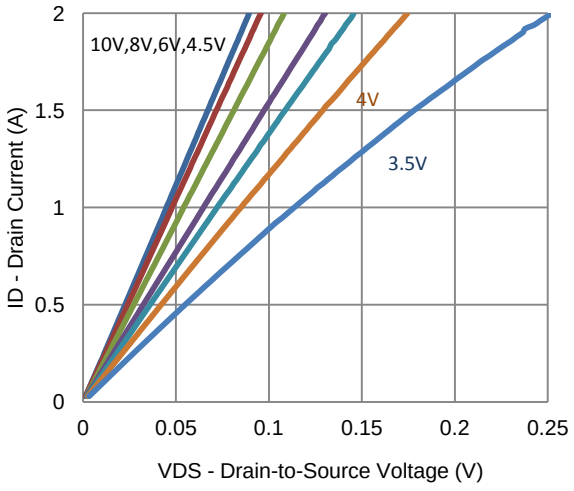
2. Transfer Characteristics



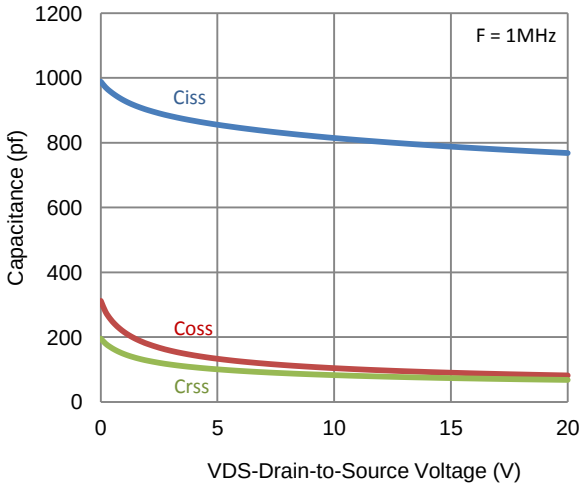
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

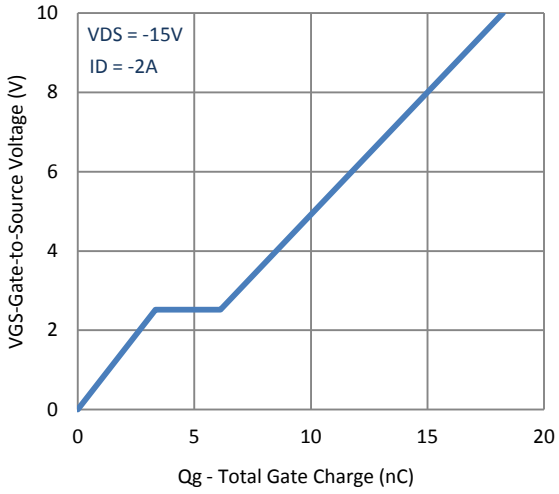


5. Output Characteristics

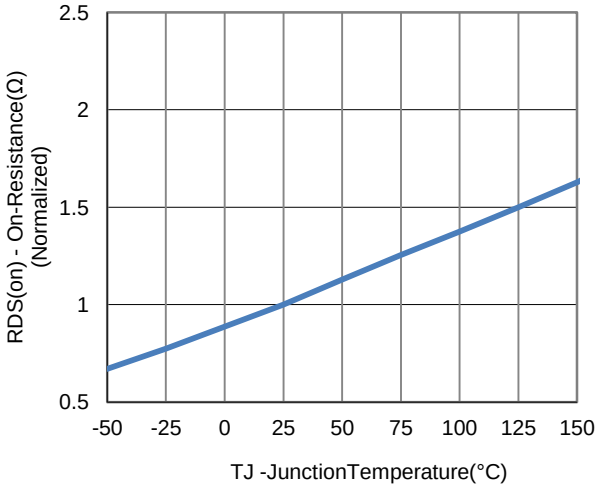


6. Capacitance

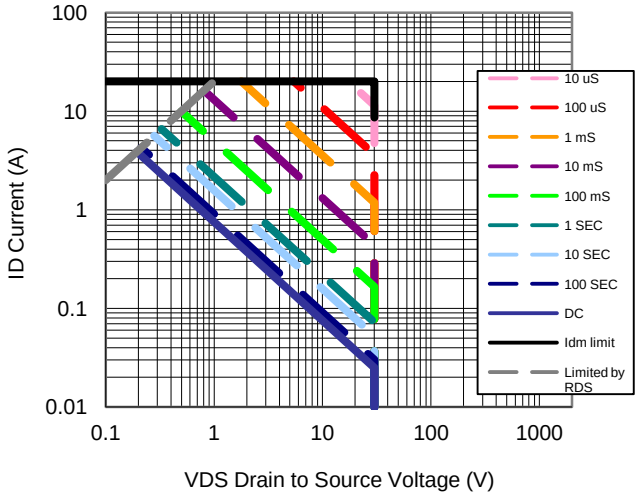
Typical Electrical Characteristics



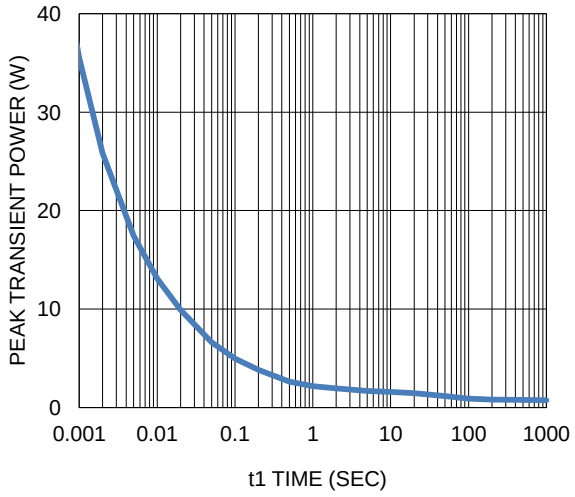
7. Gate Charge



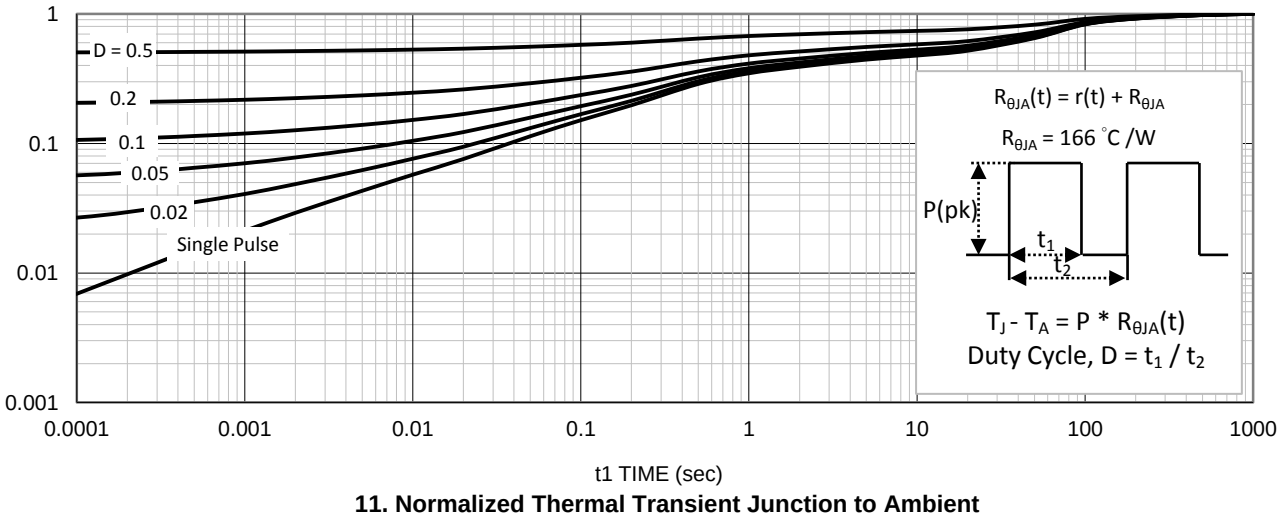
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information

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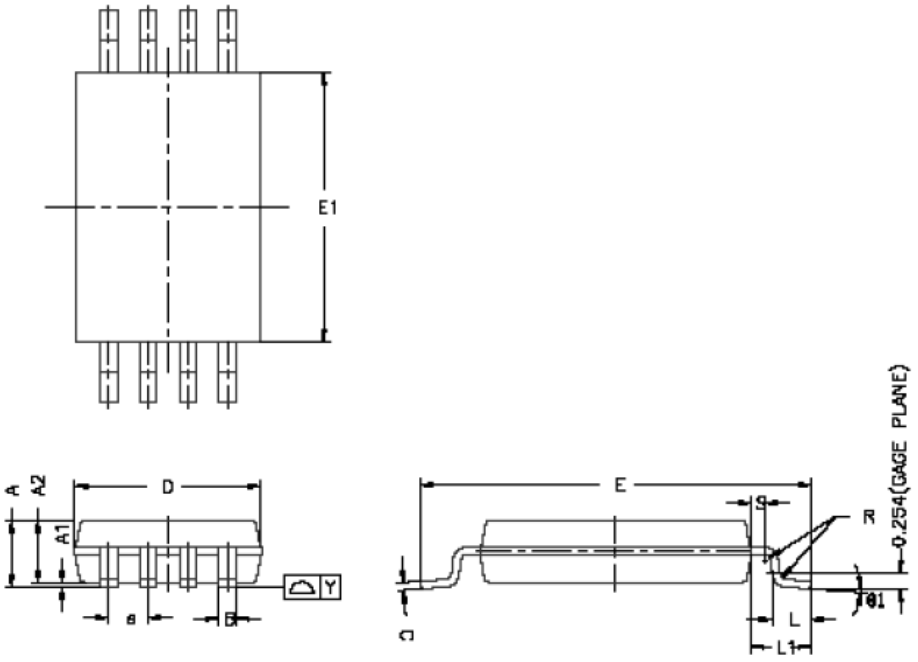
TSSOP-8: 8LEAD



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.05	1.10	1.20
A(1)	0.05	0.10	0.15
A(2)	0.99	1.02	1.05
B	0.19	0.25	0.30
C	---	0.127	---
D	2.90	3.00	3.10
E	6.20	6.40	6.60
E1	4.30	4.40	4.50
e	0.65BSC		
L	0.45	0.60	0.75
L1	0.90	1.00	1.10
Y	---	---	0.10
θ1	0°	4°	8°
R	0.09	---	---
S	0.20	---	---